

IN THE TITLE

Please change the title of the present application as follows:

FROM

METHOD AND DEVICE FOR IMPROVED SALICIDE RESISTANCE ON  
POLYSILICON GATES

TO

A DEVICE HAVING RECESSED SPACERS FOR IMPROVED SALICIDE  
RESISTANCE ON POLYSILICON GATES

IN THE CLAIMS

Claims 9 and 13 have previously been canceled without prejudice.

Please amend the following claims which are pending in the present

application:

- E<sup>1</sup> Sub G<sup>1</sup>*
8. (Three Times Amended) A gate electrode, comprising:  
a gate layer disposed above a substrate, said gate layer having a substantially level upper surface;  
a conductive layer disposed over said gate layer, said conductive layer extending beyond edges of said gate layer;  
thin first spacers disposed in contact with opposite sides of said gate layer and below said conductive layer; and  
thick second spacers disposed in contact with said thin first spacers, each thick second spacer having a uniform width throughout its height.

- E<sup>2</sup> Sub G<sup>1</sup>*
10. (Three Times Amended) The gate electrode of claim 8, wherein said gate layer comprises polysilicon.

11. (Twice Amended) The gate electrode of claim 10, wherein said conductive layer comprises polycide.

12. (Three Times Amended) The gate electrode of claim 8, wherein said thin first spacers comprise oxide.

13. (Three Times Amended) The gate electrode of claim 11, wherein said polycide comprises titanium salicide ( $\text{TiSi}_2$ ).

123. (Amended) The gate electrode of claim 8, wherein said thick second spacers comprise nitride.

124. (New) The gate electrode of claim 8, wherein the thin first spacers are at least as high as the thick second spacers.

125. (New) The gate electrode of claim 8, wherein the thick second spacers are at least twice as thick as the thin first spacers.

126. (New) The gate electrode of claim 125, wherein the thick second spacers are between 300 and 2000 Å thick.

127. (New) The gate electrode of claim 126, wherein the thick second spacers are at least 800 Å thick.

128. (New) The gate electrode of claim 125, wherein the thick second spacers are at least 800/100 times as thick as the thin first spacers.